

Hands-On Tutorials: First-principles computation of quantum materials

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Contents

1. Linux常用命令及PBS系统简介
2. Introduction to *ab initio* electronic structure calculation
3. VASP计算基本流程
4. VASP输入、输出文件及结果后处理
5. Examples: 量子材料(拓扑/磁性材料)的第一性原理计算研究
[详见 上机练习教程]

Appendix 辅助网站

1. Linux常用命令及PBS系统简介

- `ls` 列出文件
- `cd` 转移目录(文件夹)
- `mkdir` 创建目录
- `mv` 移动文件/目录/重命名
- `pwd` 当前目录的绝对路径
- `cp` 复制
- `rm` 删除 (注意不可逆, 慎用)
- `cat` 显示/合并文件

常用快捷操作

- **Ctrl + c** : 终止当前命令
- **Tab键**: 命令补齐

• .. ~

```
cd ~; cd ..; cd /home/dftcourse/Users/
```

```
mkdir test
```

```
mv test/ test1/
```

```
cp ./INCAR ../INCAR_bak
```

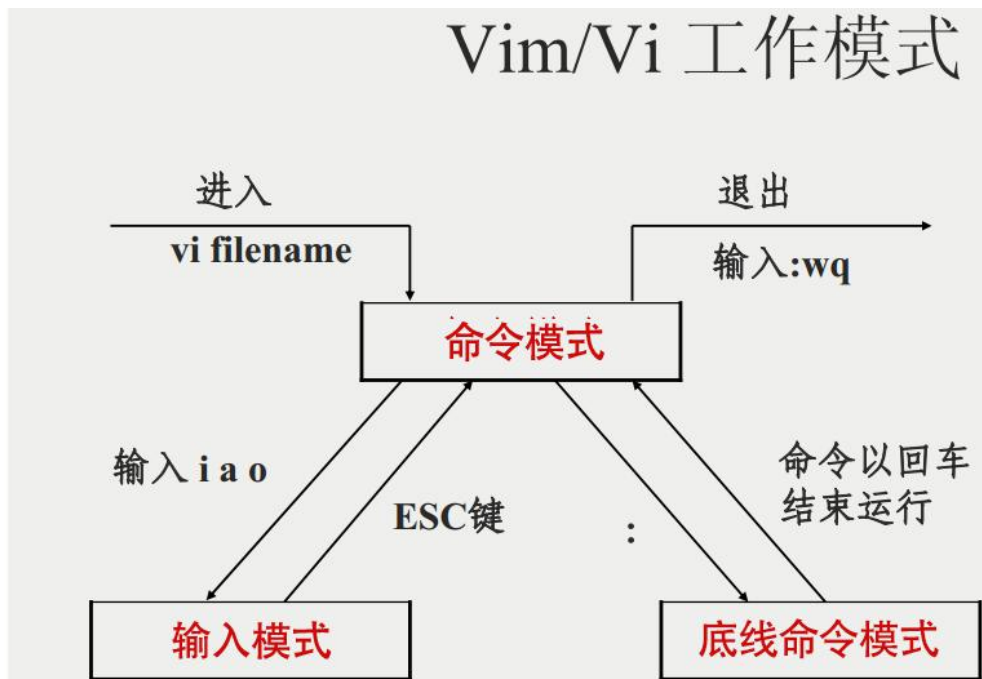
```
cp -r test1/ test2/
```

```
rm -r test1/
```

```
cat A B > C
```

```
cat A B >> C
```

- vi/vim 文本编辑



- grep 文本搜索
- more, less 分页查看文件
- head, tail 显示文件开头/结尾
- diff 比较文件不同
- sz, rz Linux系统与本机间的文件传输

在直接复制粘贴PDF或word文档中的命令或字符使用时, 请加以小心

PBS作业管理系统

- PBS脚本run.sh

```
$ cat run.sh
#PBS -N example
#PBS -l nodes=1:ppn=24
#PBS -l walltime=24:00:00
```

作业名称
节点数:核数
作业最长运行时间

- qsub 交作业
- qstat 查询作业状态 进阶版命令 j

qsub run.sh

```
$ j
w003:
Job ID      Username Queue  Jobname  SessID NDS TSK  Req'd  Req'd  Elap
-----
859509.w003 dftcours cmt     example  16550  1  24   90gb   24:00  R 00:00 node28/0*24
```

- qdel 杀作业(作业号)

qdel 859509

2. Introduction to *ab initio* electronic structure calculation

$$(H_{\text{KS}}^{\sigma} - \varepsilon_i^{\sigma})\psi_i^{\sigma}(\mathbf{r}) = 0,$$

$$H_{\text{KS}}^{\sigma}(\mathbf{r}) = -\frac{1}{2}\nabla^2 + V_{\text{KS}}^{\sigma}(\mathbf{r}),$$

$$V_{\text{KS}}^{\sigma}(\mathbf{r}) = V_{\text{ext}}(\mathbf{r}) + V_{\text{Hartree}}(\mathbf{r}) + V_{\text{xc}}^{\sigma}(\mathbf{r}).$$

✓ Choice of basis sets

- Plane waves and related basis functions

Plane waves + pseudopotentials eg. VASP, Quantum espresso, abinit, CASTEP, ...

(Linearized) augmented plane waves - (L)APW's eg. Wien2K, Elk, ...

(Linearized) muffin-tin orbitals - (L)MTO's

Projector augmented waves -PAW's

- Localized orbitals

eg. FHI-aims, Gaussian, ABACUS...

Atomic orbitals - LCAO's

OpenMX, ...

Gaussian orbitals

- ...

✓ Choice of XC functionals

Deficiencies of Kohn-Sham DFT

- ✓ exact DFT
- ✓ exact Kohn-Sham theory
- ✓ exchange-correlation approximations (LDA, GGA, ...)

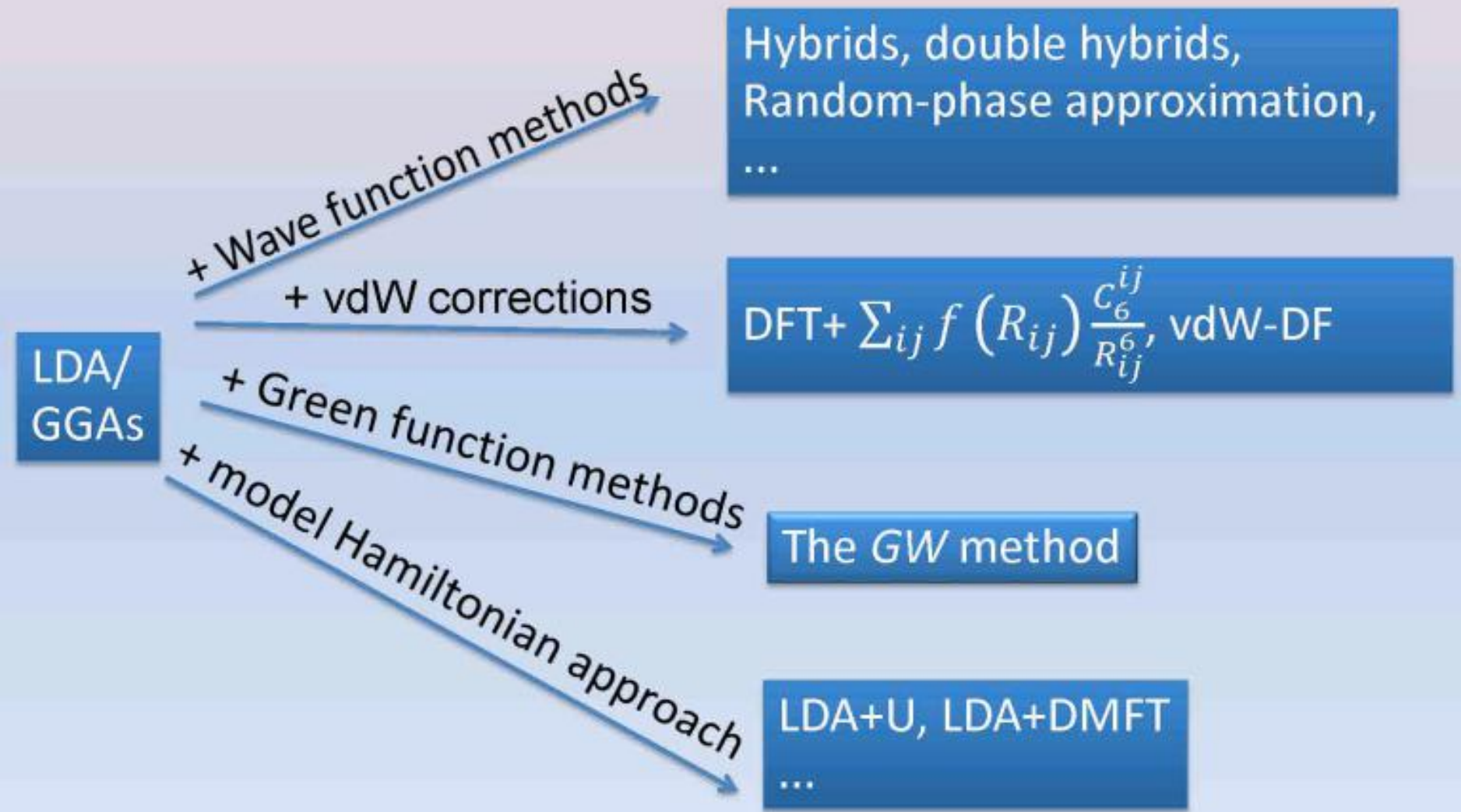
- Self-interaction error (delocalization error)

- Too small band gaps
- Underestimated reaction barrier heights
- Unable to describe localized electronic states
- Overestimated polarizability
- The XC potential decays too fast
(no negative ions, no Rydberg states)

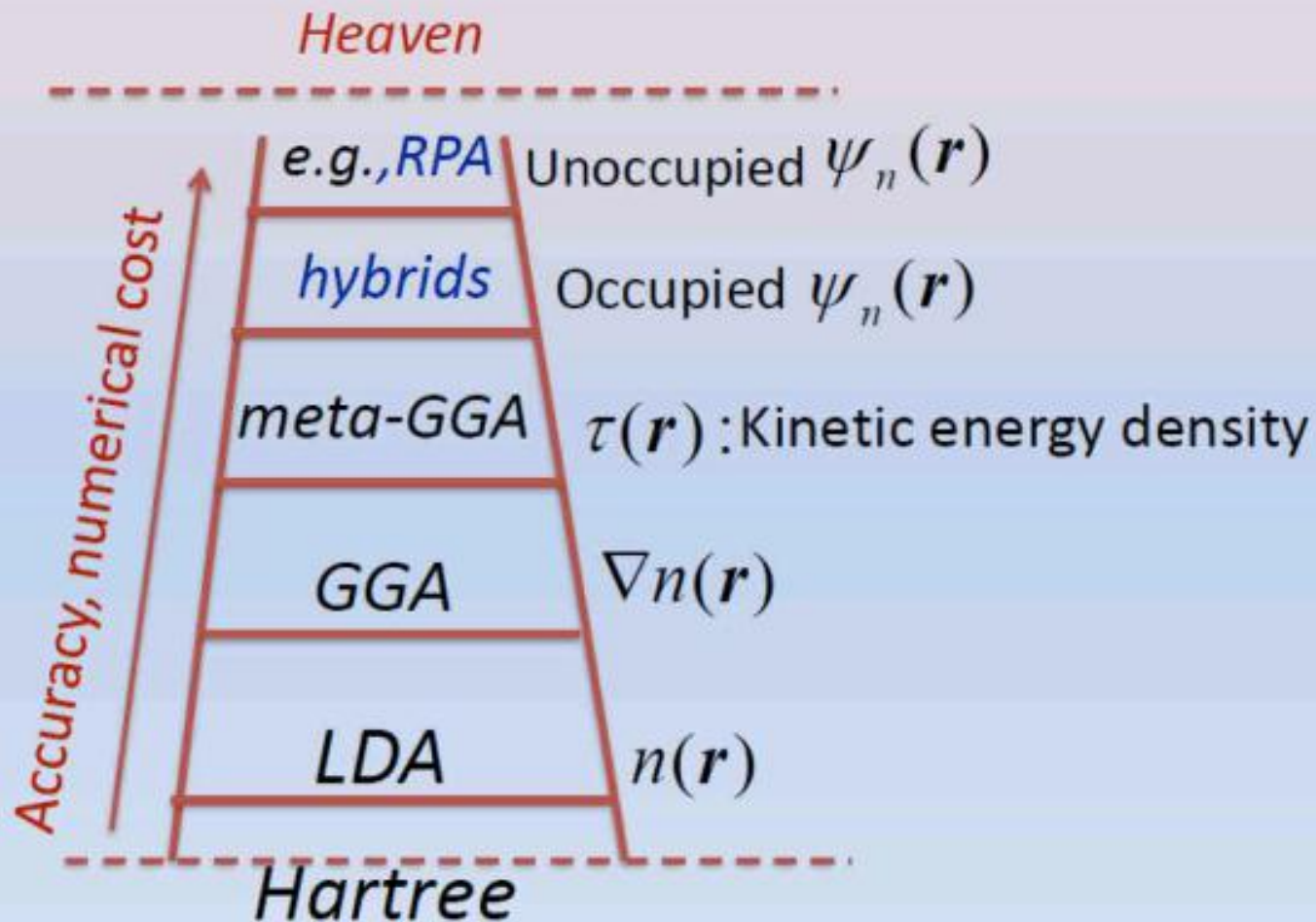
*Cohen, Mori-Sánchez, and Yang, Science **321**, 792 (2008).*

- Unable to describe “strong correlation”
(open-shell *d* and *f* electron systems)
- Absence of van der Waals interactions
- No access to excited states in general

Computational schemes beyond LDA and GGAs



Jacob's ladder of DFT



J. Perdew & K. Schmidt, *Density functional theory and its application to materials*, edited by V. Van Doren et al. (2001)



VASP = Vienna Ab-initio Simulation Package

VASP is a complex package for performing ab-initio quantum-mechanical molecular dynamics (MD) simulations using pseudopotentials (如超软赝势 US-PP) or the projector-augmented wave (PAW) method and a plane wave basis set.

<https://www.vasp.at/>

3. 第一性原理软件基本流程: 以VASP为例

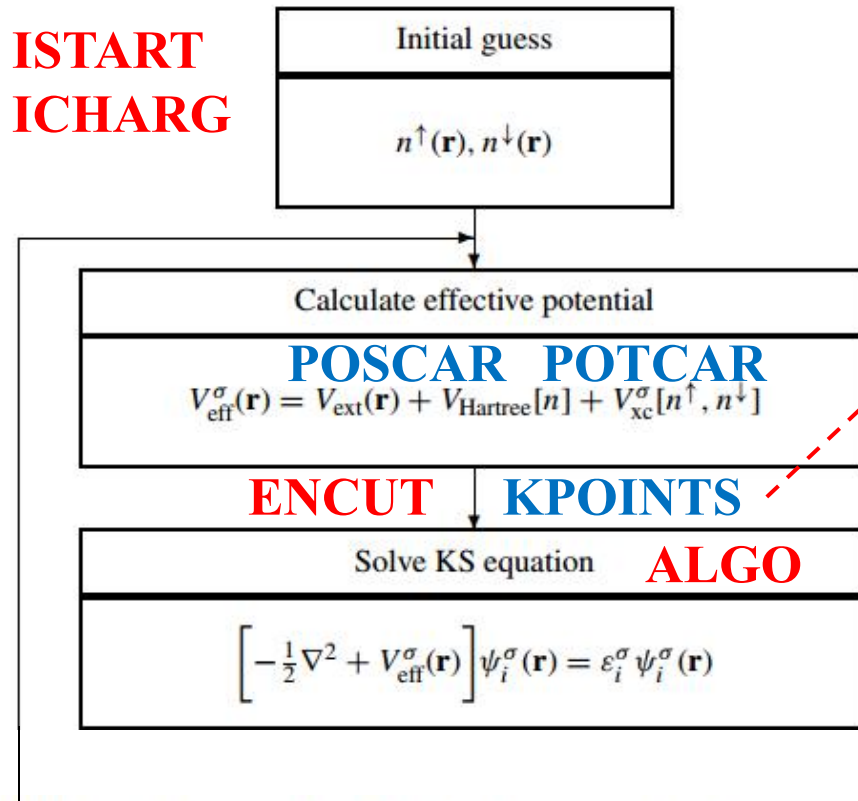


- Input files:
- ◆ **INCAR** steering the calculations
 - ◆ **POSCAR** structural data basis vectors and positions
 - ◆ **POTCAR** pseudopotential file
 - ◆ **KPOINTS** Brillouin zone sampling

Electronic step: The self-consistent loop for solution of KS equations

**ISTART
ICHARG**

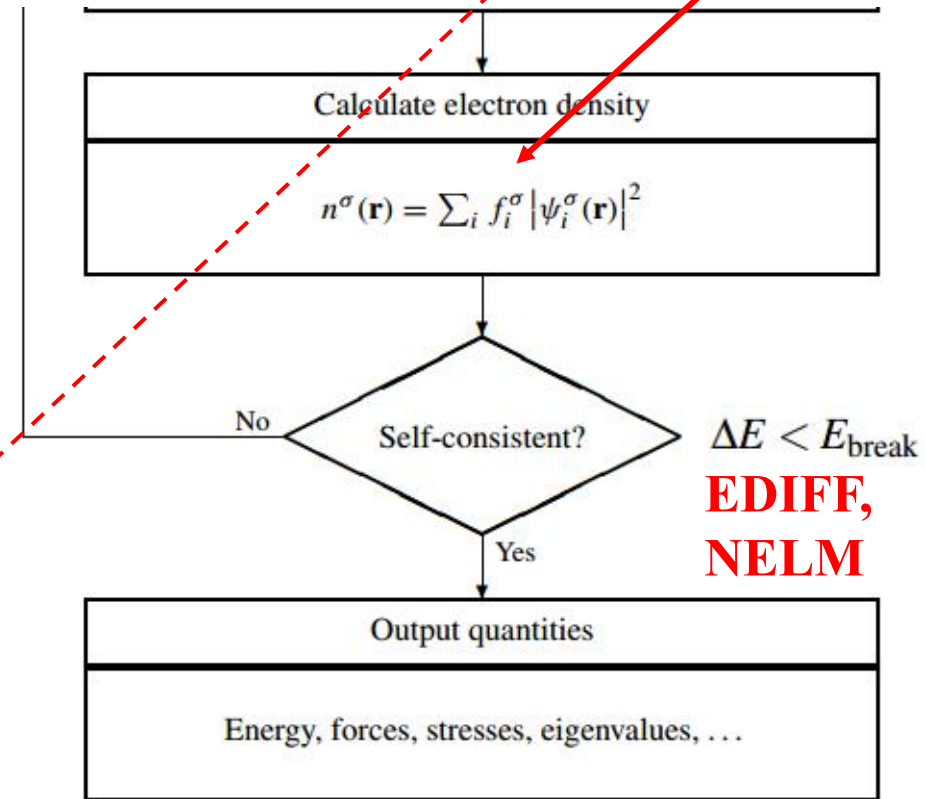
Self-consistent Kohn–Sham equations



mixing of charge density $\rho_{\text{in}}, \rho_{\text{out}} \Rightarrow \text{new } \rho_{\text{in}}$

**AMIX,
AMIX_MAG,
BMIX,
BMIX_MAG ...**

ISMEAR, SIGMA



$\Delta E < E_{\text{break}}$
**EDIFF,
NELM**

**Ionic step: IBRION, ISIF
EDIFFG,
NSW**

4. VASP基本输入、输出文件及后处理

4.1 POSCAR POTCAR

POSCAR

```
Zr2 Si2 Te2 #header
1.000 #scaling
3.6986 0.0000 0.0000
0.0000 3.6986 0.0000
0.0000 0.0000 24.8871 #a1,a2,a3
Zr Si Te #atom type
2 2 2 #atom number
Direct # Cartesian
0.25 0.75 0.4140696
0.75 0.25 0.5859304
0.75 0.75 0.5000000
0.25 0.25 0.5000000
0.75 0.25 0.3597371
0.25 0.75 0.6402629
```

Direct: $\vec{R} = x_1 \vec{a}_1 + x_2 \vec{a}_2 + x_3 \vec{a}_3$

Cartesian: $\vec{R} = s \begin{pmatrix} x_1 \\ x_2 \\ x_3 \end{pmatrix}$

VESTA: other formats (eg. cif) -> VASP POSCAR

4. VASP基本输入、输出文件及后处理

4.1 POSCAR POTCAR

POSCAR

```
Zr2 Si2 Te2 #header
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0.75 0.75 0.5000000
0.25 0.25 0.5000000
0.75 0.25 0.3597371
0.25 0.75 0.6402629
```

POTCAR

/home/dftcourse/Users/Tutorial/POTCARs
目录下

```
cat Zr/POTCAR
    Si/POTCAR
    Te/POTCAR >>
POTCAR
```

与POSCAR中元素类型一一对应

VESTA: other formats (eg. cif) -> VASP POSCAR

POTCAR

- 根据方法不同有Ultra-soft赝势(USPP)和投影缀加波的赝势(PAW)
- 根据交换关联函数的不同有LDA和GGA
- 根据处理了半芯态有A, A_sv和A_pv的不同
- 根据ENMAX的大小有A, A_s和A_h的不同

PAW W 19Jan2001

6.000000000000000000

parameters from PSCTR are:

VRHFIN = W: 5p6s5d

LEXCH = CA

EATOM = 206.5370 eV, 15.1800 Ry

TITEL = PAW W 19Jan2001

LULTRA = F use ultrasoft PP ?

IUNSCR = 1 unscreen: 0-lin 1-nonlin 2-no

RPACOR = 2.330 partial core radius

POMASS = 183.850; ZVAL = 6.000 mass and valenz

RCORE = 2.750 outmost cutoff radius

RWIGS = 2.750; RWIGS = 1.455 wigner-seitz radius (au A)

ENMAX = 223.126; ENMIN = 167.344 eV

RCLOC = 2.147 cutoff for local pot

.....

Description

1 E TYP RCUT TYP RCUT

2 .000 23 2.500

.....

ENCUT

POTCAR

- 根据方法不同有Ultra-soft赝势(USPP)和投影缀加波的赝势(PAW)
- 根据交换关联函数的不同有LDA和GGA
- 根据处理了半芯态有A, A_sv和A_pv的不同
- 根据ENMAX的大小有A, A_s和A_h的不同

```
PAW_PBE W 08Apr2002
6.000000000000000
parameters from PSCTR are:
VRHFIN =W : 6s5d
LEXCH  = PE
EATOM  = 204.6103 eV, 15.0384 Ry

TITEL  = PAW_PBE W 08Apr2002
LULTRA = F use ultrasoft PP ?
IUNSCR = 1 unscreen: 0-lin 1-nonlin 2-no
RPACOR = 2.330 partial core radius
POMASS = 183.850; ZVAL = 6.000 mass and valenz
RCORE = 2.750 outmost cutoff radius
RWIGS = 2.750; RWIGS = 1.455 wigner-seitz radius (au A)
ENMAX = 223.057; ENMIN = 167.293 eV
RCLOC = 2.147 cutoff for local pot
LCOR = T correct aug charges
LPAW = T paw PP
EAUG = 373.438
DEXC = 0.000
RMAX = 2.801 core radius for proj-oper
RAUG = 1.300 factor for augmentation sphere
RDEP = 2.886 radius for radial grids
RDEPT = 2.230 core radius for aug-charge
```

ENCUT

grep ENMAX POTCAR

https://www.vasp.at/wiki/index.php/Available_PAW_potentials

4.2 INCAR

注意不同流程中的参数变化！

结构弛豫

```
ICHARG = 2  # 2-atom 11-nsc
ENCUT = 400 # from POTCAR
ISMEAR = 0  # smearing method
SIGMA = 0.05 # broadening in eV
IBRION = 2   # CG
ISIF = 2     # 晶格弛豫参数 2,3,4
NSW = 50     # 最大弛豫次数
EDIFFG = -0.01 # 弛豫精度
NELM = 50    # 最大电子步次数
EDIFF = 1E-5 # 电子步精度
LCHARG = .FALSE. # 不输出电荷密度
LWAVE = .FALSE. # 不输出波函数
```



静态自洽（晶格固定）

```
ICHARG = 2
ENCUT = 400
ISMEAR = 0
SIGMA = 0.05
IBRION = -1 # 不再弛豫
ISIF = 2
NSW = 0     # 不再弛豫
EDIFFG = -0.01
NELM = 50
EDIFF = 1E-5
LCHARG = .TRUE. # 输出电荷密度
LWAVE = .FALSE.
```

4.2 INCAR

注意不同流程中的参数变化！

静态自洽（晶格固定）

```
ICHARG = 2
ENCUT = 400
ISMEAR = 0
SIGMA = 0.05
IBRION = -1 #不再弛豫
ISIF = 2
NSW = 0 #不再弛豫
EDIFFG = -0.01
NELM = 50
EDIFF = 1E-5
LCHARG = .TRUE. #输出电荷密度
LWAVE = .FALSE.
```



能带（非自洽计算）

```
ICHARG=11 # 11-nsc 2-atom
ENCUT = 400
ISMEAR = 0
SIGMA = 0.05
IBRION = -1
ISIF = 2
NSW = 0
EDIFFG = -0.01
NELM = 50
EDIFF = 1E-5
LCHARG = .FALSE.
LWAVE = .FALSE.
```

不懂的参数先去看**vasp wiki**

https://www.vasp.at/wiki/index.php/The_VASP_Manual

◆ The most important parameters, source of errors

A compromise between speed and accuracy

VASP GUIDE Chapter 8

✓ ENCUT

$$\psi_{n\mathbf{k}}(\mathbf{r}) = u_{n\mathbf{k}}(\mathbf{r})e^{i\mathbf{k}\mathbf{r}} \quad \text{with } u_{n\mathbf{k}}(\mathbf{r} + \mathbf{R}) = u_{n\mathbf{k}}(\mathbf{r}).$$

$$u_{n\mathbf{k}}(\mathbf{r}) = \frac{1}{\Omega^{1/2}} \sum_{\mathbf{G}} C_{\mathbf{G}n\mathbf{k}} e^{i\mathbf{G}\mathbf{r}} \quad \psi_{n\mathbf{k}}(\mathbf{r}) = \frac{1}{\Omega^{1/2}} \sum_{\mathbf{G}} C_{\mathbf{G}n\mathbf{k}} e^{i(\mathbf{G}+\mathbf{k})\mathbf{r}}$$

$$E_{cut} = \frac{\hbar^2 G_{\max}^2}{2m}$$

$$|\vec{G} + \vec{k}| \leq G_{\max}$$

```
grep ENMAX POTCAR
```

* Pulay stress: cell shape and volume relaxations
(increase ENMAX by 30%)

◆ The most important parameters, source of errors

✓ Number of k-points, and method for smearing: ISMEAR, SIGMA

$$\sum_n \frac{1}{\Omega_{BZ}} \int_{\Omega_{BZ}} \epsilon_{n\mathbf{k}} \Theta(\epsilon_{n\mathbf{k}} - \mu) d\mathbf{k}, \rightarrow \sum_n \sum_{\mathbf{k}} w_{\mathbf{k}} \epsilon_{n\mathbf{k}} \Theta(\epsilon_{n\mathbf{k}} - \mu)$$

partial occupation: replace the step function $\Theta(\epsilon_{n\mathbf{k}} - \mu)$ by a (smooth) function $f(\{\epsilon_{n\mathbf{k}}\})$

- ISMEAR: -5 tetrahedron method with Blöchl corrections # Γ -center k-mesh
 0 Gaussian smearing

1..N method of Methfessel-Paxton order N.

- SIGMA: width of smear $f\left(\frac{\epsilon - \mu}{\sigma}\right) = \frac{1}{2} \left(1 - \operatorname{erf}\left[\frac{\epsilon - \mu}{\sigma}\right]\right)$

-
- For semiconductors or insulators use the tetrahedron method (ISMEAR=-5), if the cell is too large (or if you use only a single or two k-points) use ISMEAR=0 in combination with a small SIGMA=0.05.
 - For relaxations *in metals* always use ISMEAR=1 or ISMEAR=2 and an appropriate SIGMA value (the entropy term should be less than 1 meV per atom). *Mind:* Avoid to use ISMEAR>0 for semiconductors and insulators, since it might cause problems.

For metals a sensible value is usually SIGMA= 0.2 (which is the default).

- For the calculations of the DOS and very accurate *total energy* calculations (no relaxation in metals) use the tetrahedron method (ISMEAR=-5).

entropy T*S in the OUTCAR file) must be small (i.e. < 1-2 meV/per atom).

✓ INCAR 结构弛豫相关

- IBRION = 2 # IBRION=1
- NSW
- EDIFFG
- ISIF

ISIF	calculate force	calculate stress tensor	relax ions	change cell shape	change cell volume
0	yes	no	yes	no	no
1	yes	trace only *	yes	no	no
2	yes	yes	yes	no	no
3	yes	yes	yes	yes	yes
4	yes	yes	yes	yes	no
5	yes	yes	no	yes	no
6	yes	yes	no	yes	yes
7	yes	yes	no	no	yes

Summary

- Calculation of the equilibrium volume:
 - Fit the energy over a certain volume range to an equation of state.
 - When internal degrees of freedom exist (e.g. c/a), the structure must be optimized. Use a conjugate-gradient algorithm (IBRION=2) and at each volume do e.g. 10 ionic steps (NSW=10) and allow change of internal parameters and shape (ISIF=4).
- Simpler but less reliable: relaxing all degrees of freedom including volume.
 - To relax all degrees of freedom use ISIF=3 (internal coordinates, shape and volume).
 - Mind pulay stress problem. Increase plane wave cutoff by 25-30% when the volume is allowed to change.

cp CONTCAR POSCAR

✓ INCAR 控制输出

LCHARG = .TRUE. #自洽步一定要存!

LWAVE = .FALSE.

LORBIT = 11

$$P_{Nlmn\mathbf{k}} \equiv \langle Y_{lm}^N | \phi_{n\mathbf{k}} \rangle$$

4.3 KPOINTS

设置布里渊区 k 点网格取样大小或能带结构计算时沿高对称方向的 k 点:

a) 手动输入即自定义各个 k 点的坐标和权重:

Example file

4

Cartesian

0.0	0.0	0.0	1.
0.0	0.0	0.5	1.
0.0	0.5	0.5	2.
0.5	0.5	0.5	4.

b) Line-mode: 在计算能带时用

https://mp.weixin.qq.com/s/Ptnj_oDZl-foaAPcp6imA

例子:

k-points along high symmetry lines	!注释行, 无特别的意义
10	!沿 G-X 特殊点之间产生 10 个 k 点
Line-mode	!程序自动产生特殊 k 点间的 k 点
Reciprocal	!各 k 点相对于倒格子基矢来写的
0.00 0.00 0.00	!Gamma
0.50 0.00 0.50	!X

c) 程序自动产生 k 点：最常用的，定义网格取样大小

例子：

Automatic generation	!注释行
0	!自动产生 k 点，这一行必须设为 0
Monhkorst-Pack	!Monhkorst-Pack 方法产生 k 点
9 9 9	!在各个基矢方向上分割各基矢的点数
0.0 0.0 0.0	!是否移动网格点以及移动多少(这里不移动)

```
(echo 102;echo 2;echo 0.03) | vaspkit
```

例子：

Automatic generation	!注释行
0	!自动产生 k 点，这一行必须设为 0
Gamma	!明确定义以 Gamma 点为中心,根据 M-P 方法产生 k 点
9 9 7	
0.0 0.0 0.0	

- Symmetry is used (for ISYM \geq 0) to reduce the number of k-points to the irreducible subset of symmetry inequivalent k-points (IBZKPT)

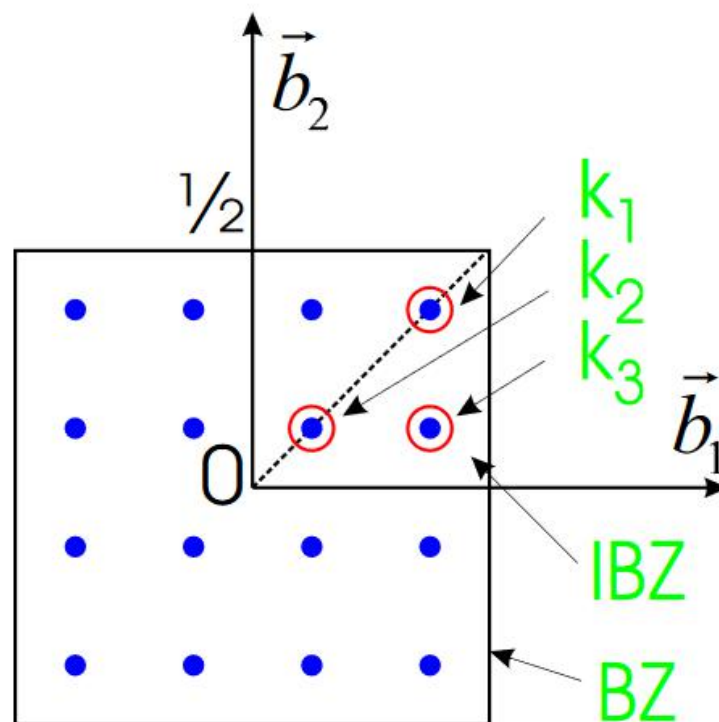
M-P方法

$$\mathbf{k}_{prs} = u_p \mathbf{b}_1 + u_r \mathbf{b}_2 + u_s \mathbf{b}_3$$

$$u_r = \frac{2r - q_r - 1}{2q_r} \quad r = 1, 2, \dots, q_r$$

\mathbf{b}_i reciprocal lattice-vectors

q_r determines number of
k-points in r-direction



IBZKPT (不可约k点)

Kpoints for relax

0 #automatic

M-P # Gamma

10 8 4 #b1,b2,b3

全奇数包含 Γ 点

Symmetry reduction of the mesh

Bravais lattice	variant	mesh choices	subsection choices
triclinic	primitive	Γ -centered, Monkhorst Pack	$ \mathbf{a}_1 ^{-1} : \mathbf{a}_2 ^{-1} : \mathbf{a}_3 ^{-1}, \mathbf{b}_1 : \mathbf{b}_2 : \mathbf{b}_3 $
monoclinic	primitive	Γ -centered, Monkhorst Pack	$ \mathbf{a}_1 ^{-1} : \mathbf{a}_2 ^{-1} : \mathbf{a}_3 ^{-1}, \mathbf{b}_1 : \mathbf{b}_2 : \mathbf{b}_3 $
	base-centered	Γ -centered, Monkhorst Pack	$ \mathbf{a}_1 ^{-1} : \mathbf{a}_2 ^{-1} : \mathbf{a}_3 ^{-1}, \mathbf{b}_1 : \mathbf{b}_2 : \mathbf{b}_3 $
orthorhombic	primitive	Γ -centered, Monkhorst Pack	$ \mathbf{a}_1 ^{-1} : \mathbf{a}_2 ^{-1} : \mathbf{a}_3 ^{-1}, \mathbf{b}_1 : \mathbf{b}_2 : \mathbf{b}_3 $
	base-centered	Γ -centered, Monkhorst Pack	$ \mathbf{a}_1 ^{-1} : \mathbf{a}_2 ^{-1} : \mathbf{a}_3 ^{-1}, \mathbf{b}_1 : \mathbf{b}_2 : \mathbf{b}_3 $
	body-centered	Γ -centered, Monkhorst Pack	$ \mathbf{a}_1 ^{-1} : \mathbf{a}_2 ^{-1} : \mathbf{a}_3 ^{-1}$
	face-centered	Γ -centered	$ \mathbf{b}_1 : \mathbf{b}_2 : \mathbf{b}_3 $
tetragonal	primitive	Γ -centered, Monkhorst Pack	$ \mathbf{a}_1 ^{-1} : \mathbf{a}_2 ^{-1} : \mathbf{a}_3 ^{-1}, \mathbf{b}_1 : \mathbf{b}_2 : \mathbf{b}_3 $
	body-centered	Γ -centered, Monkhorst Pack	$ \mathbf{a}_1 ^{-1} : \mathbf{a}_2 ^{-1} : \mathbf{a}_3 ^{-1}$
hexagonal	rhombohedral	Γ -centered	$ \mathbf{a}_1 ^{-1} : \mathbf{a}_2 ^{-1} : \mathbf{a}_3 ^{-1}, \mathbf{b}_1 : \mathbf{b}_2 : \mathbf{b}_3 $
	hexagonal	Γ -centered	$ \mathbf{a}_1 ^{-1} : \mathbf{a}_2 ^{-1} : \mathbf{a}_3 ^{-1}, \mathbf{b}_1 : \mathbf{b}_2 : \mathbf{b}_3 $
cubic	primitive	Γ -centered, Monkhorst Pack	$ \mathbf{a}_1 ^{-1} : \mathbf{a}_2 ^{-1} : \mathbf{a}_3 ^{-1}, \mathbf{b}_1 : \mathbf{b}_2 : \mathbf{b}_3 $
	body-centered	Γ -centered, Monkhorst Pack	$ \mathbf{a}_1 ^{-1} : \mathbf{a}_2 ^{-1} : \mathbf{a}_3 ^{-1}, \mathbf{b}_1 : \mathbf{b}_2 : \mathbf{b}_3 $
	face-centered	Γ -centered	$ \mathbf{a}_1 ^{-1} : \mathbf{a}_2 ^{-1} : \mathbf{a}_3 ^{-1}, \mathbf{b}_1 : \mathbf{b}_2 : \mathbf{b}_3 $

<https://www.vasp.at/wiki/index.php/KPOINTS>

4.4 输出文件及后处理

(*.*.* # for PBS)

stdout (output.*)

OUTCAR

OSZICAR

CHGCAR

WAVECAR

DOSCAR

PROCAR

CONTCAR

vasprun.xml

...



Input parameter

Symmetry

TOTEN

LOOP TIME

.....

```
grep * OUTCAR | tail
```

individual parts are separated by lines

- first part: reading INCAR, POTCAR, POSCAR
- nearest neighbor distances and analysis of symmetry
- information on what was parsed from INCAR
- verbose job information
- information on lattice, k-points and positions
- information on the basis set (number of plane waves)
- non local pseudopotential information
- information for each electronic step (one line in OSZICAR)

```
grep -A2 TOTEN OUTCAR
```

```
free energy TOTEN = -11.15933907 eV
energy without entropy= -11.15101726 energy(sigma->0) = -11.15517817
```

```
tail -1 OSZICAR
```

```
1 F= -.11159339E+02 E0= -.11155178E+02 d E =-.832181E-02
```

Post-processing for VASP

vaspkit

<https://vaspkit.com/index.html>

```
      \\\\/\\
      /  (.) (.)  \
+-----o000o--()--o000o-----+
|      A Pre- and Post-Processing Program for VASP Code      |
|      VASPKIT Version: 0.73 (20 Apr. 2019)                  |
|      Developed by Vei WANG (wangvei@me.com)                |
|      Contributor: Nan XU (tamas@zju.edu.cn)                 |
+-----o000o-----+
      (  )  Oooo.
      \ (  (  )
      \_)  ) /
      (/_

===== Structural Options =====
1) VASP Input Files Generator      2) Elastic-Properties
3) K-Path Generator                4) Structure Editor
5) Catalysis-ElectroChemi Kit     6) Symmetry Search

===== Electronic Options =====
11) Density-of-States              21) DFT Band-Structure
23) 3D Band-Structure              25) Hybrid-DFT Band-Structure
26) Fermi-Surface                  28) Band-Structure Unfolding

===== Charge & Potential & Wavefunction Options =====
31) Charge & Spin Density          42) Potential-Related
51) Wave-Function Analysis

===== Misc Utilities =====
71) Linear Optics                  72) Molecular-Dynamics Kit
73) VASP2BoltzTraP Interface
91) Semiconductor Calculator        92) 2D-Materials Kit

0) Quit
----->>
```

注意:

- (1) 支持命令行模式
- (2) band减掉的Fermi level自行解决

```
echo -e "\n" $(sed -n 6p DOSCAR | awk '{print $4}') > FERMI_ENERGY.in
```

5. Examples

(1) diamond & fcc Si

(2) Xene (graphene, silicene, germanene, stanene)

(3) Bi_2Se_3 family

(4) MnBi_2Te_4 family

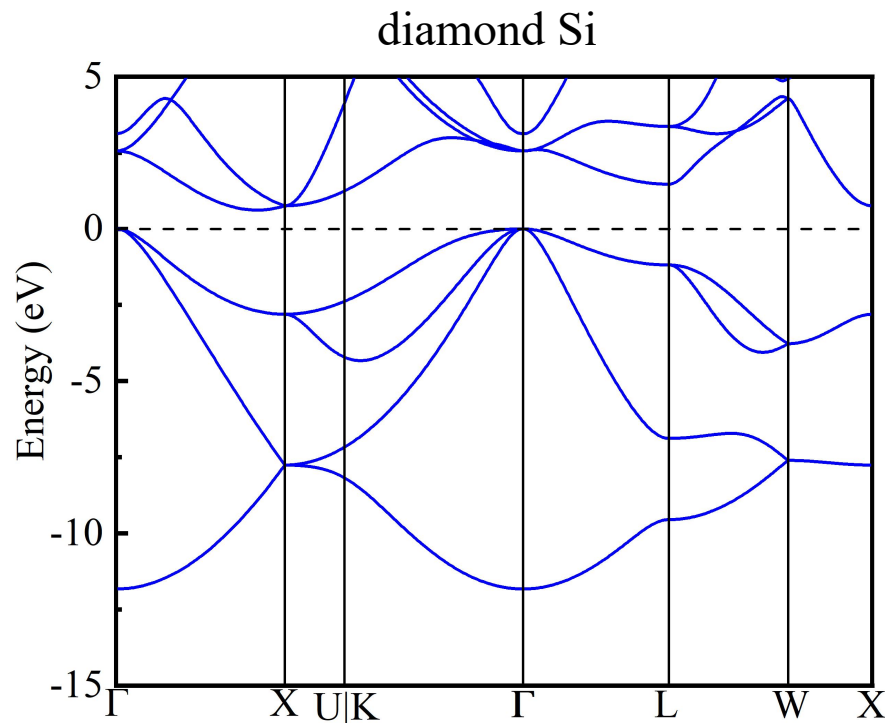
(1) diamond & fcc Si

1. relax: ① relax all degrees of freedom;
② E - V curve & EOS fitting.

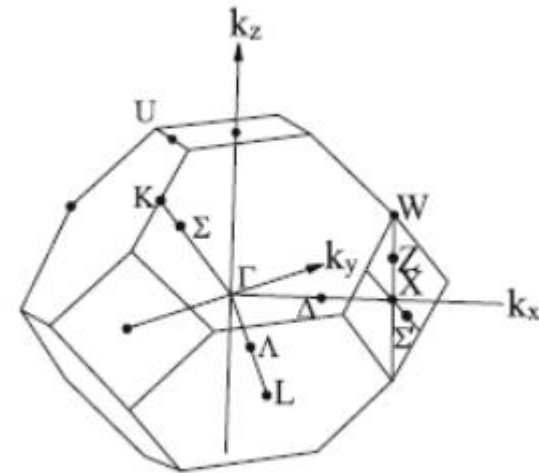
<http://vaspkit.cn/index.php/48.html>

2. self-consistency (sc):
check settings of ENCUT & KPOINTS (smearing methods)

3. band:



band degeneracy & symmetry



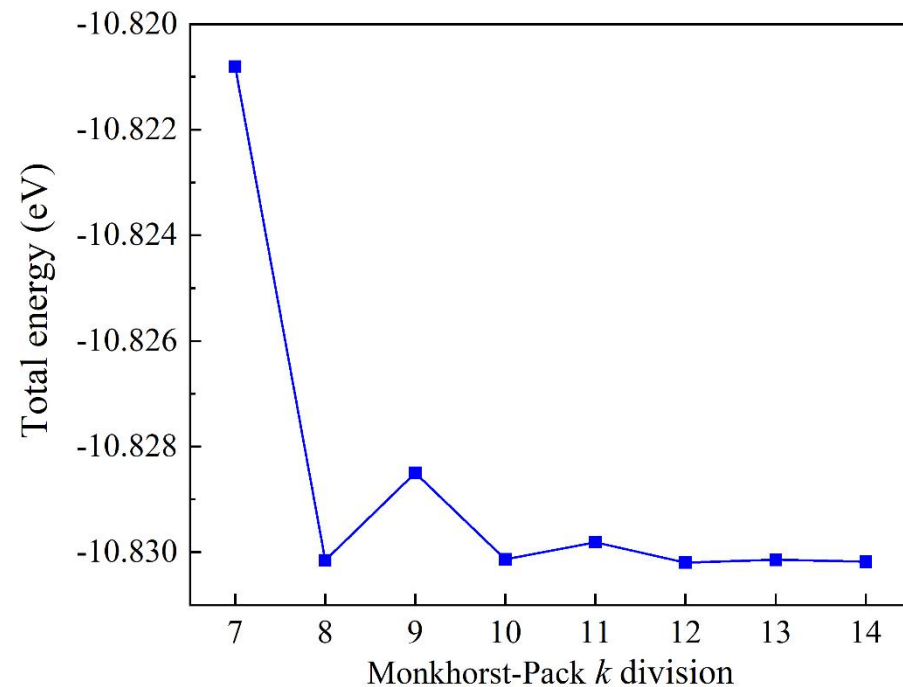
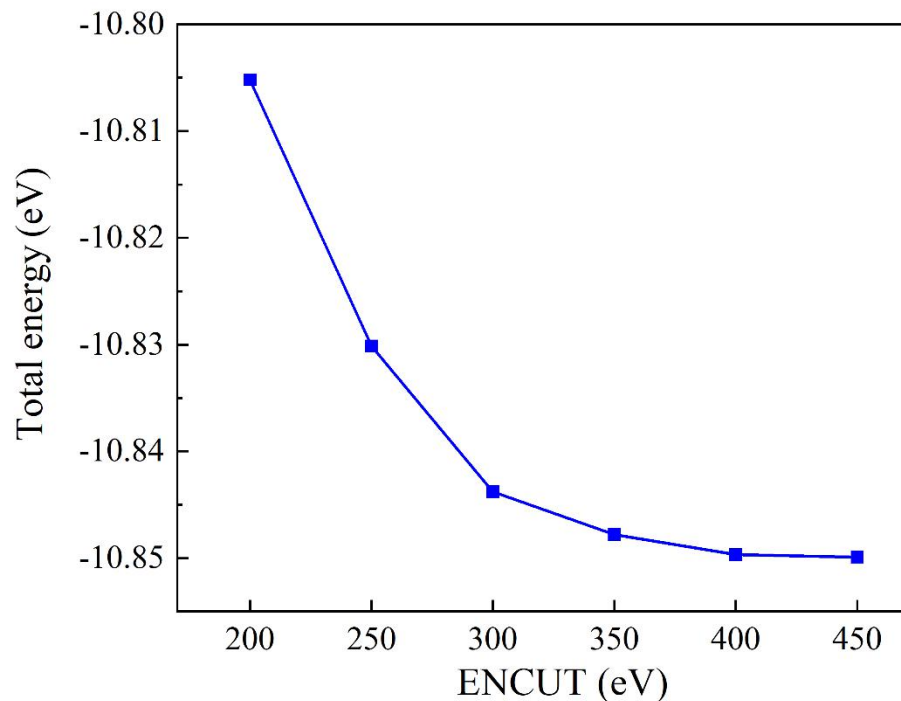
https://www.vasp.at/wiki/index.php/Cd_Si
https://www.vasp.at/wiki/index.php/Fcc_Si

(1) diamond & fcc Si

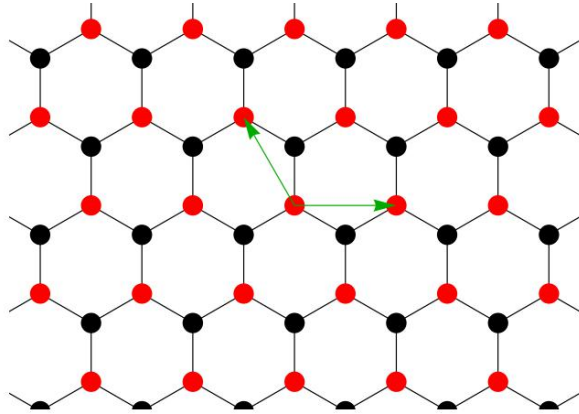
4. test: check settings of

- ① ENCUT
- ② KPOINTS & smearing methods (ISMEAR & SIGMA)

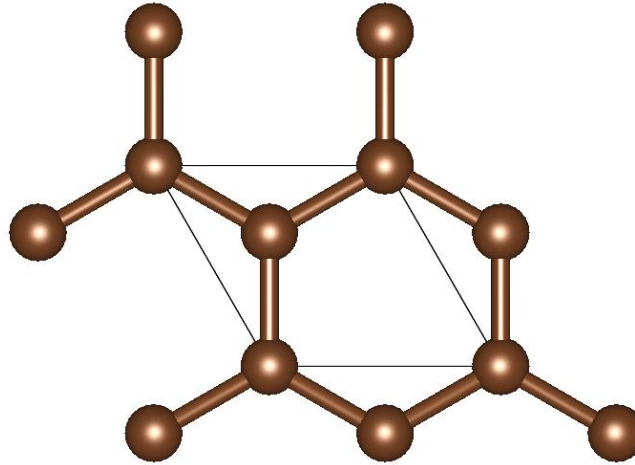
diamond Si (ISMEAR = 0 ; SIGMA = 0.05)



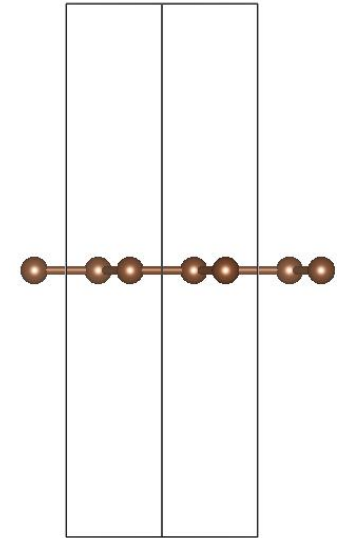
(2) Xene (graphene, ..., stanene)



2D honeycomb lattice



ab-plane

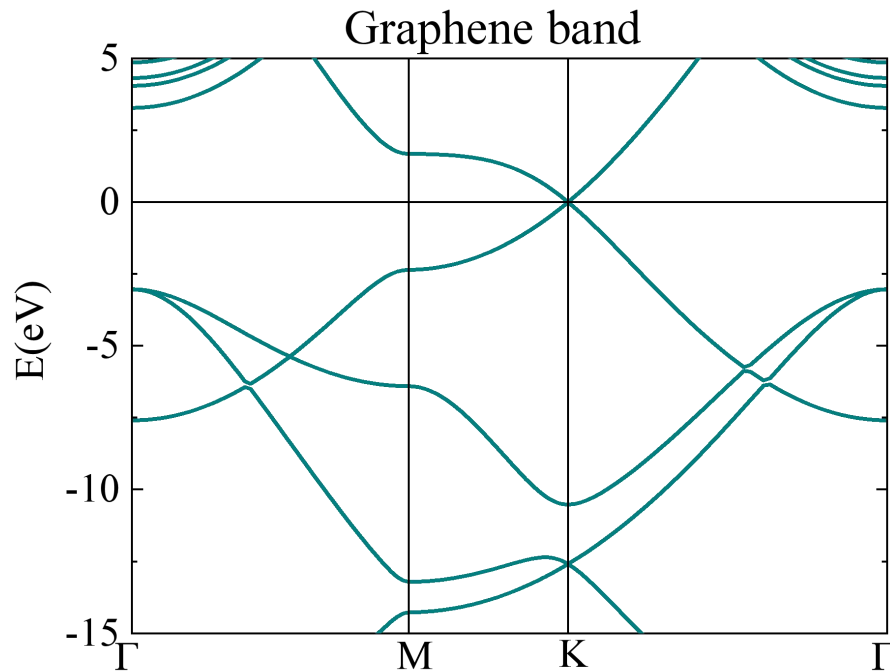


ac-plane

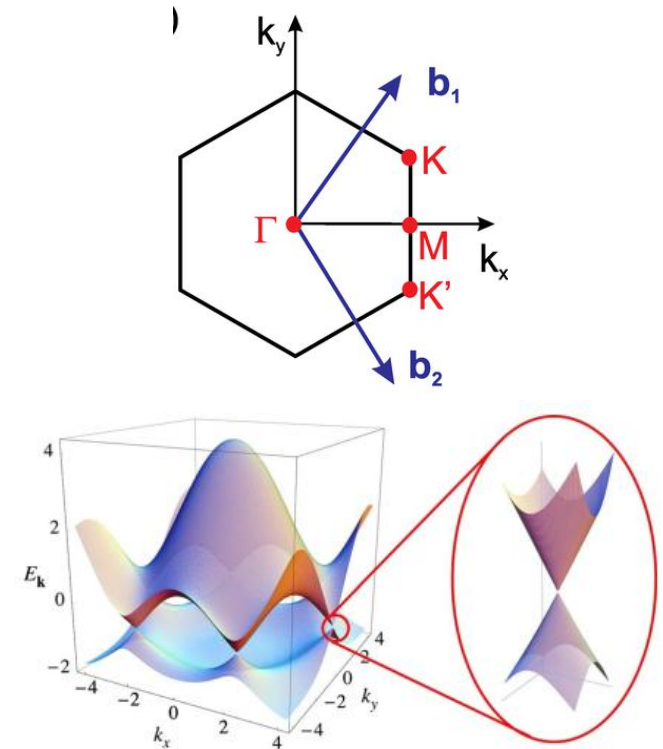
➤ Graphene

- check the setting of the thickness of the vacuum layer
- relax the lattice constant: $\text{ISIF} = 4$
- band projection

LORBIT = 11



- Dirac point at K
- saddle point at M



Rev. Mod. Phys. **81**, 109 (2009)

✓ Strain engineering of Dirac points

- biaxial strain: keep all symmetries
- uniaxial strain: break C_{3z} symmetry

✓ multilayer graphene

- van der Waals interactions

<https://www.vasp.at/wiki/index.php/IVDW>

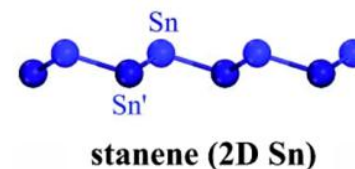
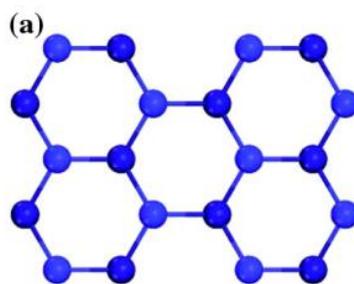
https://www.vasp.at/wiki/index.php/Nonlocal_vdW-DF_functionals

- Interlayer stacking and effect of interlayer coupling

➤ Stanene

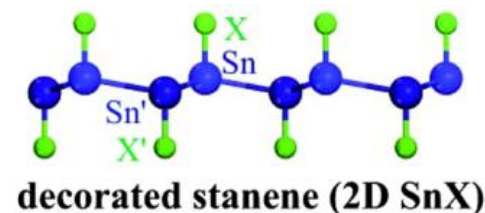
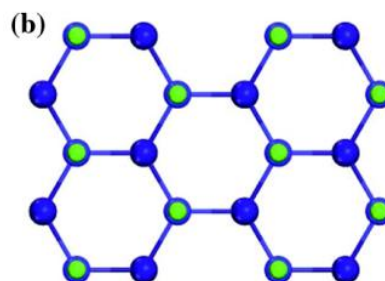
✓ 2D Sn

- structural buckling
- spin-orbit coupling (SOC) effect

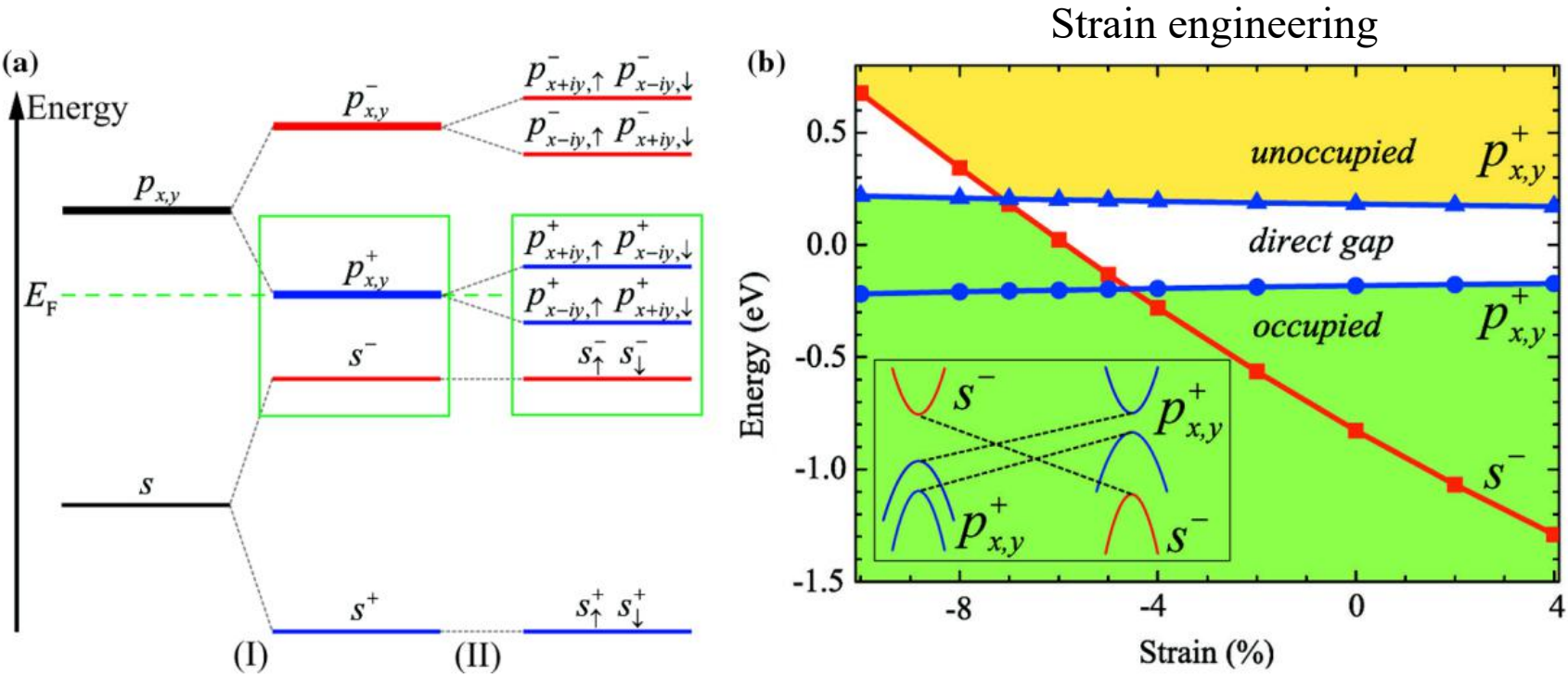
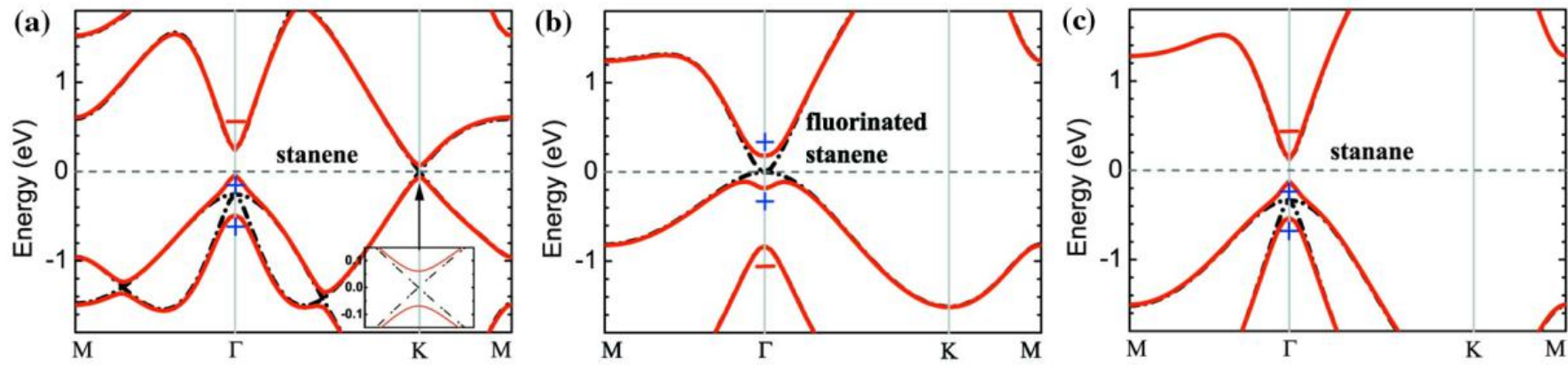


```
LSORBIT = .TRUE.  
MAGMOM = 6*0
```

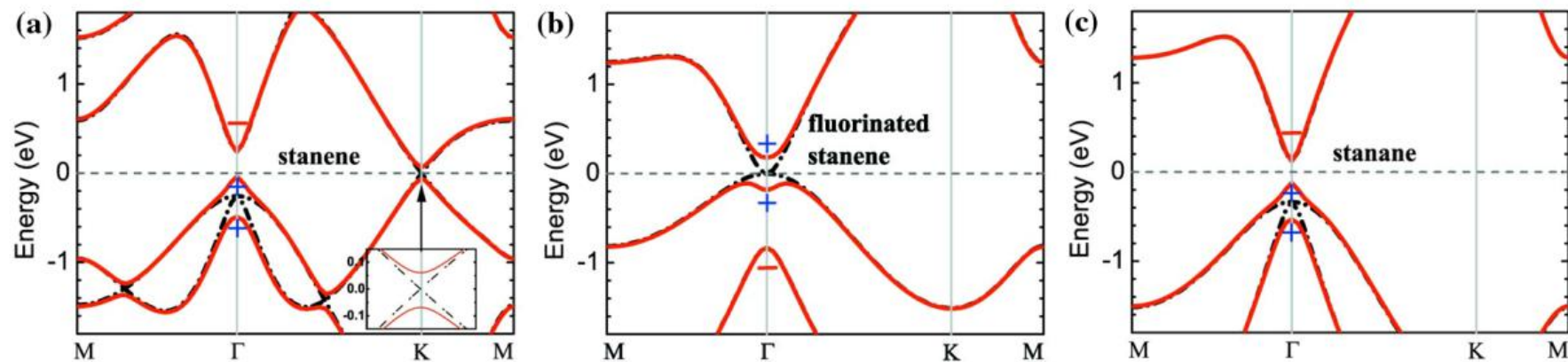
✓ Decorated stanene (SnX)



✓ Topological properties of stanene: quantum spin Hall insulators



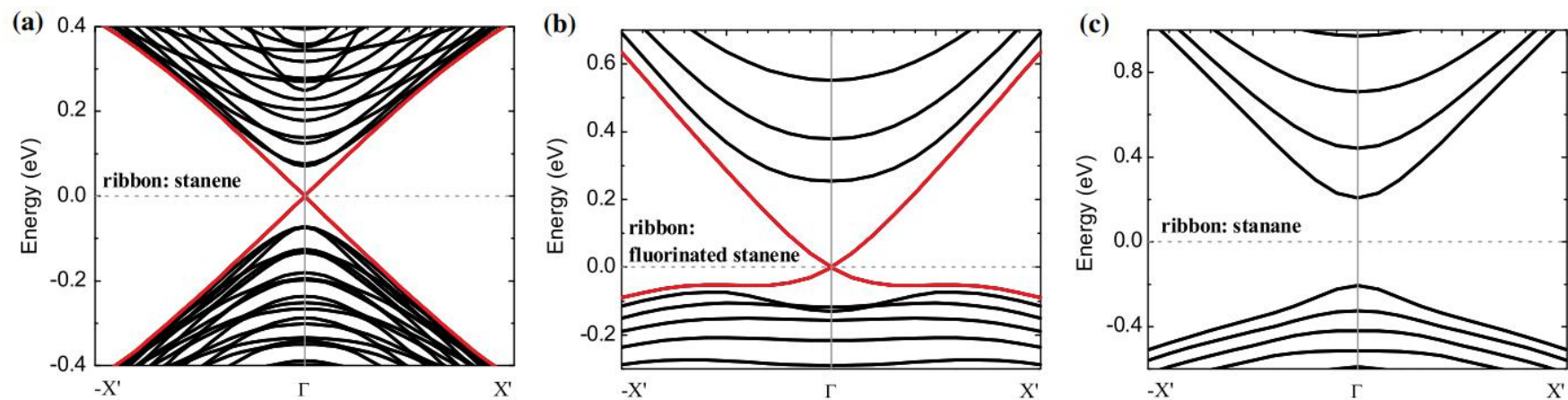
✓ Topological properties of stanene: quantum spin Hall insulators



Sn

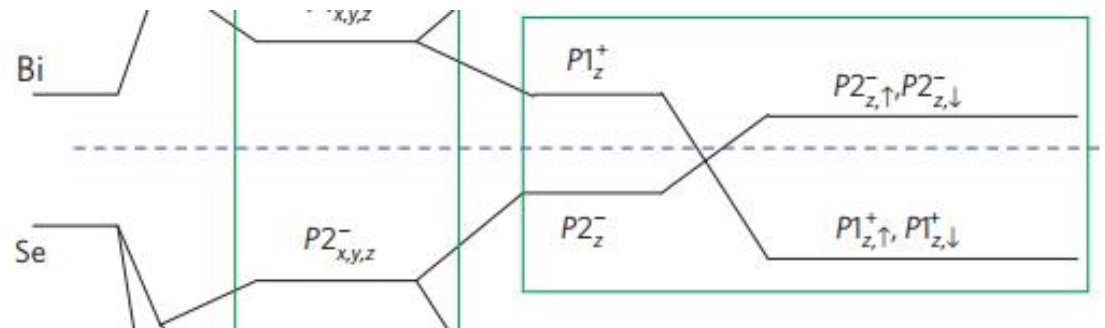
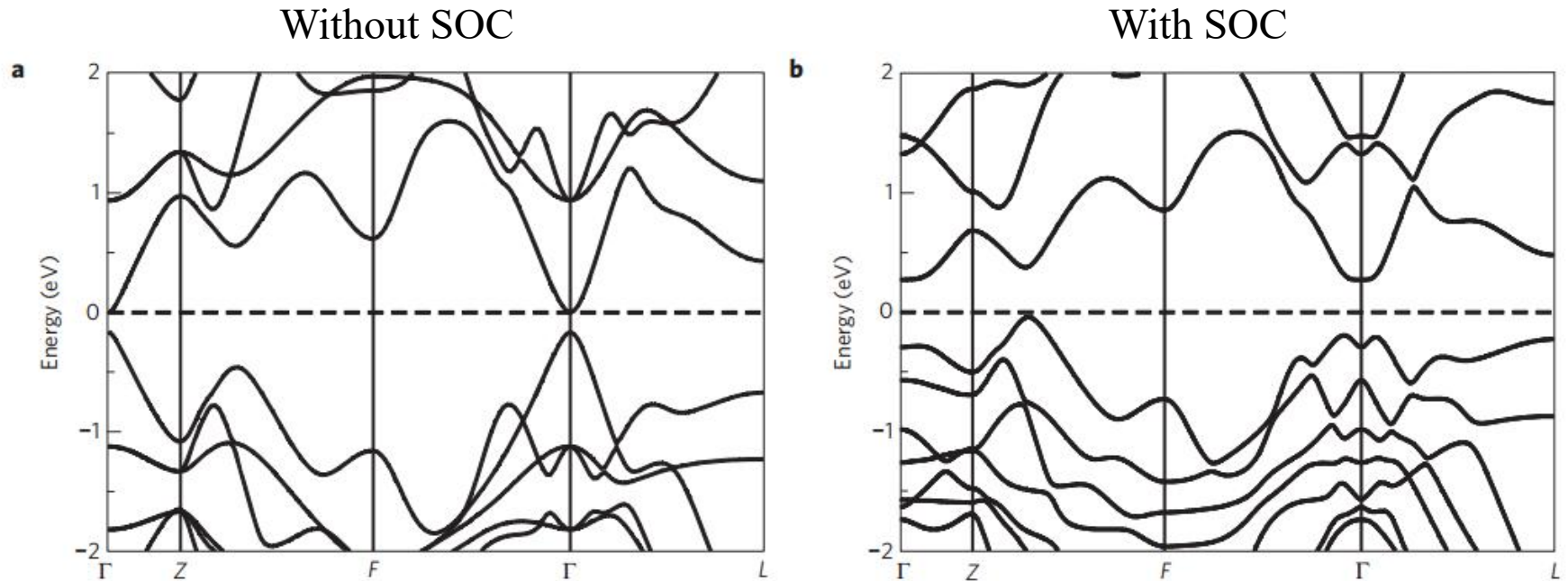
SnF

SnH



(3) Bi_2Se_3 family: 3D strong TI

✓ SOC induced band inversion

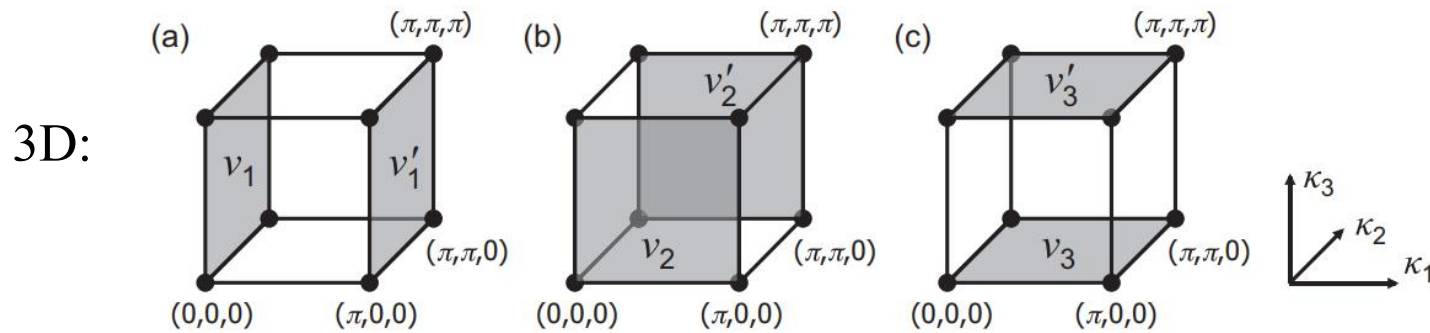


Evolution of orbitals at Γ

(3) Bi_2Se_3 family: 3D strong TI

✓ Z_2 invariant & topological surface states

With inversion symmetry: 2D: $(-1)^\nu = \prod_{a=1}^4 \prod_m^{N_{\text{occ}}/2} \xi_{am}$



$$(-)^{\nu_0} = (-)^{\nu_1+\nu'_1} = (-)^{\nu_2+\nu'_2} = (-)^{\nu_3+\nu'_3}$$

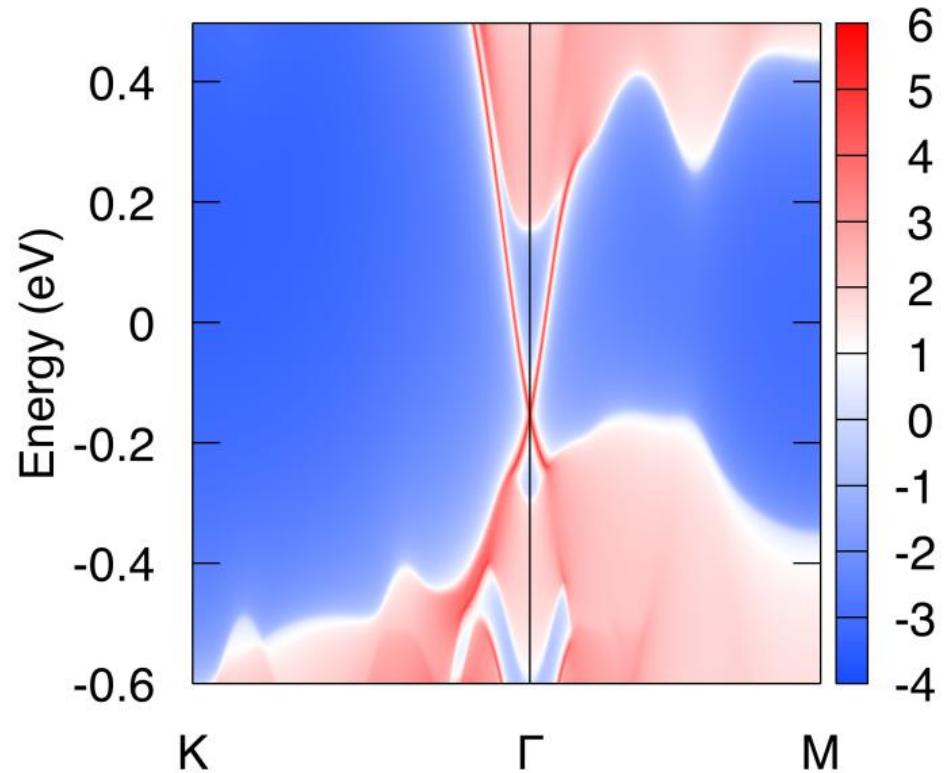
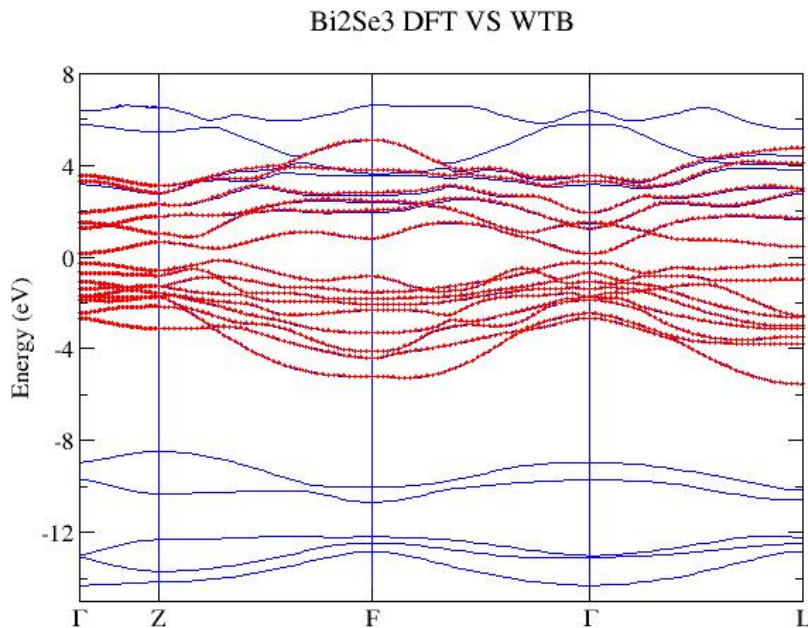
$(\nu_0; \nu'_1 \nu'_2 \nu'_3)$ ν_0 odd is known as a *strong TI*

Berry phases in electronic structure theory, book by David Vanderbilt

- calculate parity at TRIM using `irvsp`

(3) Bi_2Se_3 family: 3D strong TI

- ✓ Z_2 invariant & topological surface states
- calculate surface states using Wannier90 + WannierTools:



(4) MnBi_2Te_4 family: magnetic topological materials

➤ DFT study of magnetism

[https://www.vasp.at/wiki/index.php/Magnetism - Tutorial](https://www.vasp.at/wiki/index.php/Magnetism_-_Tutorial)

- spin-polarized calculation

AFM

```
ISPIN = 2  
MAGMOM = 2.0 -2.0 2*0
```

FM

```
ISPIN = 2  
MAGMOM = 2.0 2.0 2*0
```

- DFT+ U method

```
LDAU = .TRUE.  
LDAUTYPE = 2  
LDAUL = 2 -1  
LDAUU = 3.0 0.0  
LDAUJ = 0.0 0.0  
LDAUPRINT = 2
```

- Noncollinear magnetism

```
LNONCOLLINEAR = .TRUE.  
MAGMOM = 1 0 0 0 1 0
```

- Effect of SOC: magnetocrystalline anisotropy

```
LSORBIT = .TRUE.  
MAGMOM = 0 0 2 0 0 -2 6*0  
SAXIS = 1.0 0.0 0.0
```

(4) MnBi_2Te_4 family: magnetic topological materials

➤ Tunable magnetic topological properties in MnBi_2Te_4

- interlayer magnetic coupling

- dimension
/thickness

维度/厚度	层间磁序	
	反铁磁	铁磁
体相	反铁磁 拓扑绝缘体	磁性拓扑外尔半金属
奇数层薄膜	陈绝缘体	陈绝缘体
偶数层薄膜	轴子绝缘体	陈绝缘体

- magnetic orientation-dependent topological properties

Sci. Adv. **5**, eaaw5685 (2019)

Phys. Rev. B **100**, 121103(R) (2019)

总结： 计算流程

1. Relax步（非必选）

INCAR（重点检查IBRION, NSW, ISIF）

KPOINTS（Gamma/MP格式）

POTCAR（例： `cat /pot_paw/PBE/B/POTCAR /pot_paw/PBE/N/POTCAR > POTCAR`）

POSCAR（记住原子和POTCAR一一对应）

run.sh（修改前几行）然后qsub run.sh

如何检查relax步？

```
reached required accuracy - stopping structural energy minimisation
```

```
grep TOTEN OUTCAR | tail
```

在OUTCAR中寻找原子受力 (TOTAL-FORCE)

最后得到的弛豫完成的文件 CONTCAR

2.sc步

修改INCAR文件（重点检查 LCHARG, NSW, IBRION）

必要时修改KPOINTS

记住cp CONTCAR POSCAR

提取费米能用于后续绘制能带

3.Band 步

修改INCAR文件（重点检查ICHARG=11）

修改KPOINTS文件（查询晶体对称性vaspkit，确定高对称路径KPATH）

4.绘制能带

vaspkit -task 211

安装xftp或用sz命令，传文件到自己的电脑上，画图！

5.报错怎么办？

报错有多种可能，报错信息写在output*以及*.o*, *.e* 中，自行翻译，有问题先想想，一般都能解决！

Appendix 辅助网站

(1) 材料数据库

<https://mp.weixin.qq.com/s/gJJhMYKrRqHfbYyJl4mwhg>

(2) 晶体对称性相关, BZ, 高对称路径

https://mp.weixin.qq.com/s/Ptnj_oDZl-foaAPcp6imA

<http://www.cryst.ehu.es/cgi-bin/cryst/programs/nph-kv-list>

(3) 晶体结构建模相关: crystaltoolkit

<https://crystaltoolkit.org/>

(4) 其它学习资料

https://mp.weixin.qq.com/s/ZCgC5Rw3898Za_ejMF1xIw